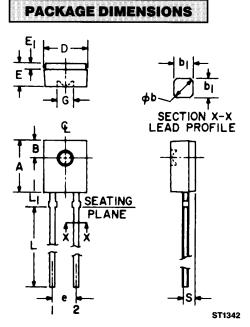


# H23A1/2



### DESCRIPTION

The H23A is a matched emitter-detector pair which consists of a gallium arsenide infrared emitting diode and a silicon phototransistor. The clear epoxy packaging system is designed to optimize the mechanical resolution, coupling efficiency, cost, and reliability. The devices are marked with a color dot for easy identification of the emitter and detector.

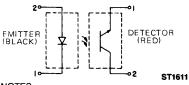
#### FEATURES

- Good optical to mechanical alignment
- Color dot for easy recognition of LED and phototransistor

Low cost

014400	MILLIMETERS		INC	WOTTO	
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
A	5.59	5.80	.220	.228	
В	1.78	NOM.	.070	NOM.	2
®b	.60	.75	.024	.030	1
b,	.51	NOM.	.020	NOM.	1
D	4.45	4.70	.175	.185	
E	2.41	2.67	.095	.105	
E1	.58	.69	.023	.027	
е	2.41	2.67	.095	.105	3
G	1.98	NOM.	.078	NOM.	
L	12.7	—	.500	—	
L,	1.40	1.65	.055	.065	
S	.83	.94	.033	.037	3





NOTES

- 1. TWO LEADS. LEAD CROSS SECTION DIMENSIONS UNCONTROLLED WITHIN 1.27 mm (0.50") OF SEATING PLANE.
- 2. CENTERLINE OF ACTIVE ELEMENT LOCATED WITHIN .25 mm (.010') OF TRUE POSITION.
- 3. AS MEASURED AT THE SEATING PLANE.
- 4. INCH DIMENSIONS DERIVED FROM MILLIMETERS.



ABSOLUTE MAXIMUM RATINGS (T <sub>a</sub> = 25°C Uni	ess Otherwise Specified)
Storage Temperature	
Operating Temperature	55°C to +100°C
Soldering:	
Lead Temperature (Iron)	
Lead Temperature (Flow)	260°C for 10 sec. <sup>(3,4</sup>
INPUT DIODE	
Continuous Forward Current	
Forward Current (pw, 1µS; 33 Hz)	
Reverse Voltage	6.0 Volt
Power Dissipation	
DUTPUT TRANSISTOR	
Collector-Emitter Voltage	
Emitter-Collector Voltage	
Power Dissipation	

ELECTRICAL CHAI	RACTERIS	TICS (	T <sub>A</sub> = 25°C Unle	ess Othen	wise Specif	fied)
PARAMETER	SYMBOL	MiN.	TYP.	MAX.	UNITS	TEST CONDITIONS
INPUT DIODE						
Forward Voltage	V <sub>F</sub>	—		1.7	v	$I_F = 60 \text{ mA}$
Reverse Leakage Current	I <sub>R</sub>	_		10	μA	V <sub>R</sub> = 6V
Reverse Breakdown Voltage	BV <sub>R</sub>	6.0			V	$I_{R} = 10 \mu A$
OUTPUT TRANSISTOR						
Emitter-Collector Breakdown	$BV_{ECO}$	6.0		_	V	$I_{E} = 100 \mu A$
Collector-Emitter Breakdown	BV <sub>CEO</sub>	30			V	$I_c = 10 \text{ mA}$
Collector-Emitter Leakage	I <sub>CEO</sub>	_		100	nA	$V_{CE} = 10 \text{ V}$
COUPLED						-15-
On-State Collector Current	I <sub>C(ON)</sub>		See page 3.			
Saturation Voltage	V <sub>CE(SAT)</sub>		See page 3.			
Turn-On Time	t <sub>on</sub>		150		μS	$I_F$ =30 mA, V <sub>cc</sub> =5V R <sub>L</sub> =2.5KΩ
Turn-Off Time	t <sub>orr</sub>		150		μS	$I_F=30$ mA, $V_{cc}=5V$ RL=2.5K $\Omega$

#### NOTES

- Derate power dissipation linearly 1.33mW/°C above 25°C.
  Derate power dissipation linearly 2.00mW/°C above 25°C.
- 3. RMA flux is recommended.

- Methanol or Isopropyl alcohols are recommended as cleaning agents.
  Soldering iron tip 1/6" (1.6 mm) minimum from housing.
  Coupled characteristics are measured at a separation distance of .155" (4 mm) with the lenses of the emitter and detector on a common axis within 0.1mm and parallel within 5°.



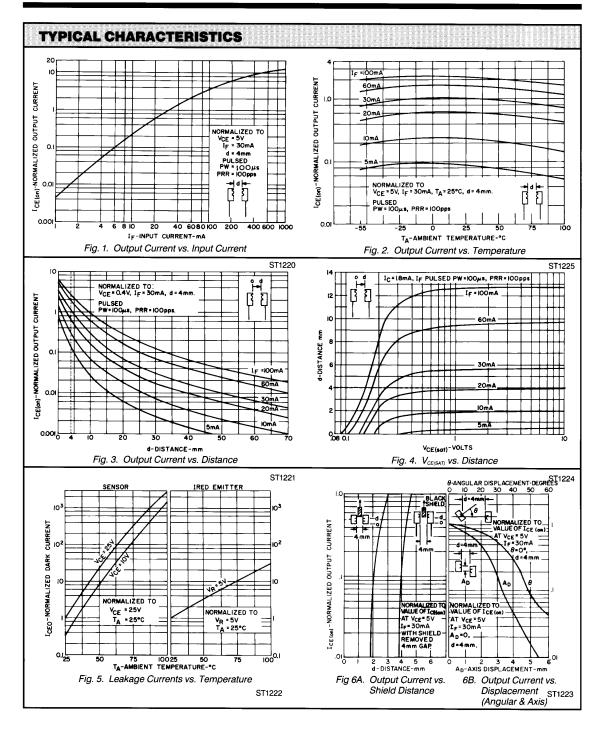
SEMICONDUCTOR

# H23A1/2

IC(ON) and VCE(BA	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
ON-STATE COLLEC	TOR CURRENT					
H23A1	C(ON)	1.5	—		mA	$I_{\rm F} = 30 {\rm mA}, V_{\rm CE} = 5 {\rm V}^{(6)}$
H23A2	I <sub>C(ON)</sub>	0.5			mA	$I_{\rm F} = 30 {\rm mA}, V_{\rm CE} = 5 V^{(6)}$
ATURATION VOLT	AGE					
H23A1			—	0.40	V	$I_{\rm F} = 30 {\rm mA}, I_{\rm C} = 1.0 {\rm mA}$
H23A2	V <sub>CE(SAT)</sub>			0.40	v	$I_{\rm F} = 30 m A, I_{\rm C} = .4 m A^{(6)}$



SEMICONDUCTOR





#### DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

#### LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.